1. General description

PNP high-voltage low V_{CEsat} transistor in a medium power SOT223 (SC-73) Surface-Mounted Device (SMD) plastic package.

NPN complement: PBHV8560Z-Q

2. Features and benefits

- · High voltage
- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C
- High collector current gain h_{FE} at high I_C
- Qualified according to AEC-Q101 and recommended for use in automotive applications

3. Applications

- · Electronic ballast for fluorescent lighting
- · LED driver for LED chain module
- LCD backlighting
- HID front lighting
- Automotive motor management
- · Hook switch for wired telecom
- Switch Mode Power Supply (SMPS)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CESM}	collector-emitter peak voltage	V _{BE} = 0 V	-	-	-600	V
V _{CEO}	collector-emitter voltage	open base	-	-	-600	V
I _C	collector current		-	-	-0.5	Α
h _{FE}	DC current gain	$V_{CE} = -10 \text{ V}; I_{C} = -50 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$	70	130	-	



600 V, 0.5 A PNP high-voltage low VCEsat transistor

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	4	C
2	С	collector		В
3	E	emitter		B —
4	С	collector	1 2 3	Ė
			SC-73 (SOT223)	sym028

6. Ordering information

Table 3. Ordering information

Type number	Package						
	Name	Description	Version				
PBHV9560Z-Q		plastic, surface-mounted package with increased heatsink; 4 leads; 2.3 mm pitch; 6.5 mm x 3.5 mm x 1.65 mm body	SOT223				

7. Marking

Table 4. Marking codes

Type number	Marking code
PBHV9560Z-Q	HV956Z

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter		-	-600	V
V_{CEO}	collector-emitter voltage	open base		-	-600	V
V _{CESM}	collector-emitter peak voltage	V _{BE} = 0 V		-	-600	V
V _{EBO}	emitter-base voltage	open collector		-	-6	V
I _C	collector current			-	-0.5	А
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	0.65	W
			[2]	-	1.4	W
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

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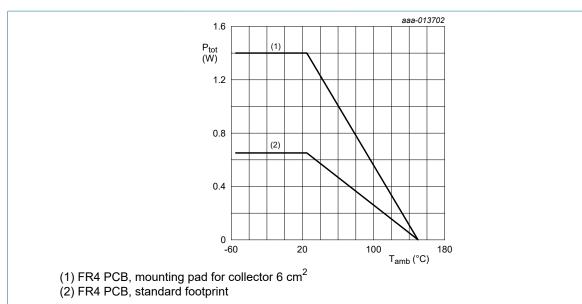


Fig. 1. Power derating curves

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from	in free air	[1]	-	-	190	K/W
	junction to ambient		[2]	-	-	89	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	20	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

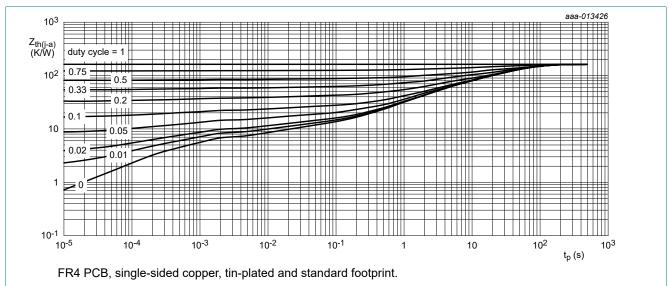
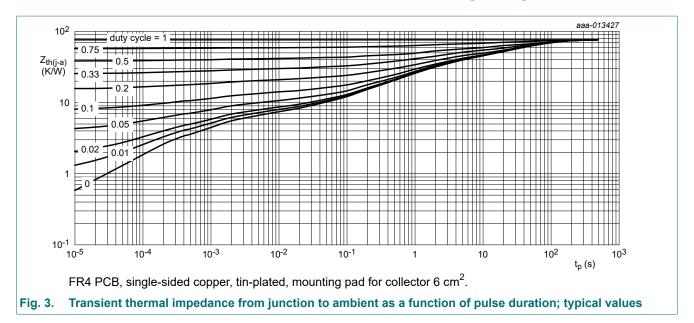


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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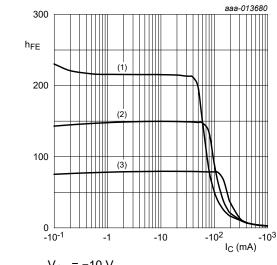
10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	V _{CB} = -400 V; I _E = 0 A; T _{amb} = 25 °C	-	-	-100	nA
	current	V _{CB} = -400 V; I _E = 0 A; T _j = 150 °C	-	-	-10	μA
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-	-	-100	nA
I _{CES}	collector-emitter cut-off current	V _{CE} = -400 V; V _{BE} = 0 V; T _{amb} = 25 °C	-	-	-100	nA
h _{FE}	DC current gain	V _{CE} = -10 V; I _C = -50 mA; T _{amb} = 25 °C	70	130	-	
		V_{CE} = -10 V; I_{C} = -100 mA; pulsed; $t_{p} \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	50	90	-	
V _{CEsat}	collector-emitter saturation voltage	I _C = -50 mA; I _B = -5 mA; T _{amb} = 25 °C	-	-150	-250	mV
		I_C = -100 mA; I_B = -20 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-140	-250	mV
V _{BEsat}	base-emitter saturation voltage	I_C = -50 mA; I_B = -5 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-	-900	mV
f _T	transition frequency	V _{CE} = -10 V; I _C = -30 mA; f = 100 MHz	-	38	-	MHz
C _c	collector capacitance	V_{CB} = -20 V; I_{E} = 0 A; i_{e} = 0 A; f = 1 MHz; T_{amb} = 25 °C	-	12	-	pF
C _e	emitter capacitance	V_{EB} = -0.5 V; I_{C} = 0 A; i_{c} = 0 A; f = 1 MHz; T_{amb} = 25 °C	-	390	-	pF

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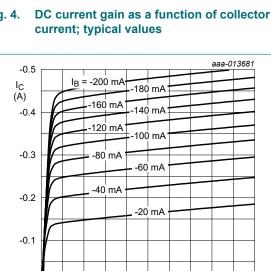
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(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 4. current; typical values



 T_{amb} = 25 °C

-1

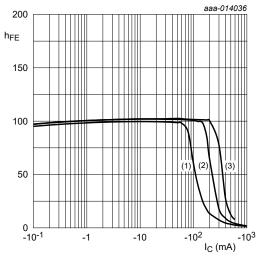
0

Fig. 6. Collector current as a function of collectoremitter voltage; typical values

-2

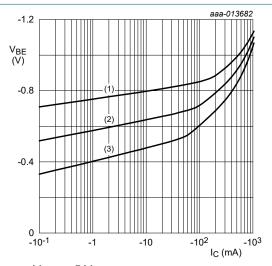
-3

-4 V_{CE} (V)



$$\begin{aligned} &h_{FE} = f_{(IC)} \\ &T_{amb} = 25 \text{ °C} \\ &(1) \text{ $V_{CE} = -10$ V} \\ &(2) \text{ $V_{CE} = -25$ V} \\ &(3) \text{ $V_{CE} = -50$ V} \end{aligned}$$

DC current gain as a function of collector Fig. 5. current; typical values



$$V_{CE} = -5 V$$

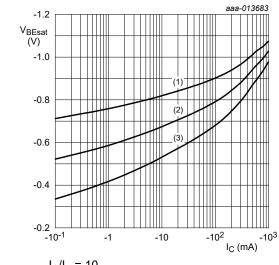
(1) $T_{amb} = -55 °C$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 7. Base-emitter voltage as a function of collector current; typical values

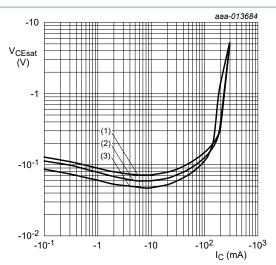
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 $I_{\rm C}/I_{\rm B} = 10$

(1) $T_{amb} = -55 \,^{\circ}\text{C}$ (2) $T_{amb} = 25 \,^{\circ}\text{C}$ (3) $T_{amb} = 100 \,^{\circ}\text{C}$

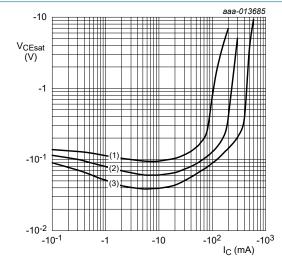
Fig. 8. Base-emitter saturation voltage as a function of Fig. 9. collector current; typical values



 $I_C/I_B = 5$

(1) $T_{amb} = 100 \text{ °C}$ (2) $T_{amb} = 25 \text{ °C}$ (3) $T_{amb} = -55 \text{ °C}$

Collector-emitter saturation voltage as a function of collector current; typical values

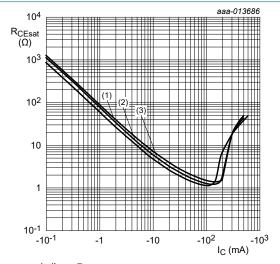


 T_{amb} = 25 °C

(1) $I_C/I_B = 10.0$ (2) $I_C/I_B = 5.0$

 $(3) I_{\rm C}/I_{\rm B} = 2.5$

Fig. 10. Collector-emitter saturation voltage as a function of collector current; typical values



 $I_C/I_B = 5$

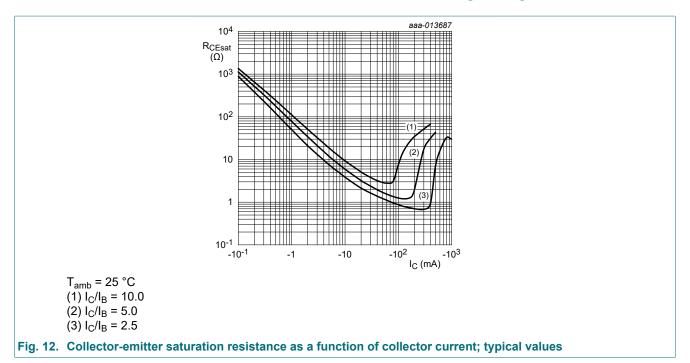
(1) T_{amb} = 100 °C

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = -55 \, ^{\circ}C$

Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values

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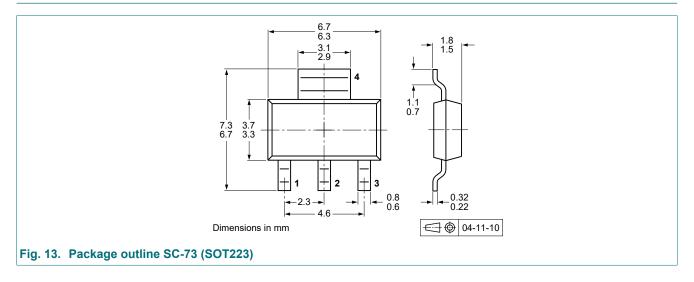


11. Test information

Quality information

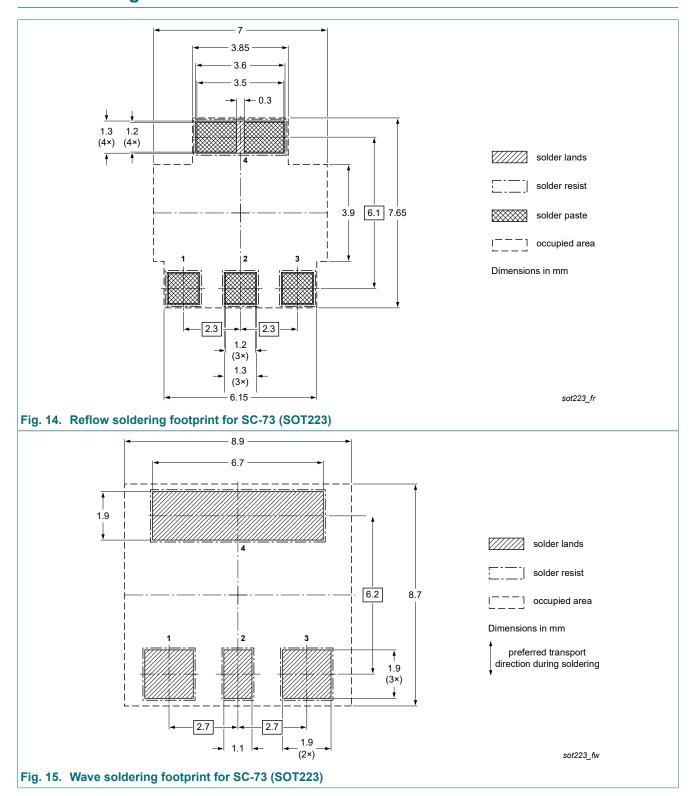
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

12. Package outline



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13. Soldering



600 V, 0.5 A PNP high-voltage low VCEsat transistor

14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBHV9560Z-Q v.1	20230714	Product data sheet	-	-

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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